NUP6101DMR2

Advance Information

Unidirectional TVS Array for High-Speed Data Line Protection

The NUP6101DMR2 transient voltage suppressor is designed to protect equipment attached to up to six high speed communication lines from ESD, EFT, and lightning.

Features:

- Micro8 Package
- Peak Power – 300 Watts 8 x 20 μS
- ESD Rating:
  IEC 61000–4–2 (ESD) 15 kV (air) 8 kV (contact)
  IEC 61000–4–4 (EFT) 40 A (5/5 ns)
  IEC 61000–4–5 (lighting) 23 A (8/20 μs)
- UL Flammability Rating of 94 V–0

Typical Applications:

- High Speed Communication Line Protection
- 5.0 V Data and I/O Lines
- Microprocessor Based Equipment
- LAN/WAN Equipment
- Servers
- Notebook and Desktop PC
- Instrumentation

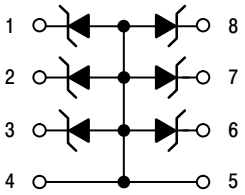
MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Power Dissipation 8 x 20 μs @ T_A = 25°C (Note 1)	P_{pk}	300	W
Peak Pulse Current 8 x 20 μs @ T_A = 25°C (Note 1)	I_{PP}	17	A
Junction and Storage Temperature Range	T_J, T_{stg}	–55 to +150	°C
Lead Solder Temperature – Maximum 10 Seconds Duration	T_L	260	°C

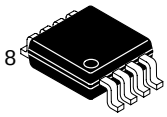
1. Non–repetitive current pulse 8 x 20 μS exponential decay waveform

ON Semiconductor™

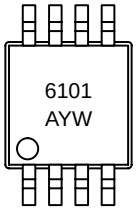
http://onsemi.com



MARKING DIAGRAM

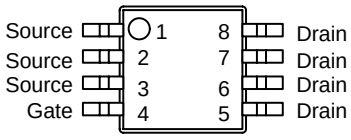


Micro8
CASE 846A



6101 = Device Code
A = Assembly Location
Y = Year
W = Work Week

PIN ASSIGNMENT



Top View

ORDERING INFORMATION

Device	Package	Shipping
NUP6101DMR2	Micro8	4000 Tape & Reel

This document contains information on a new product. Specifications and information herein are subject to change without notice.

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Min	Typ	Max	Unit
Reverse Stand–off Voltage	V_{BRWM}	–	–	5.0	V
Reverse Breakdown Voltage @ I_t = 1.0 mA	V_{BR}	6.0	–	–	V
Reverse Leakage Current @ V_{RWM} = 5.0 Volts, T = 25°C	I_R	–	–	20	μA
Maximum Clamping Voltage @ I_{PP} = 1.0 A, 8 x 20 μS	V_C	–	–	9.8	V
Maximum Clamping Voltage @ I_{PP} = 5.0 A, 8 x 20 μS	V_C		–	11	V
Maximum Peak Pulse Current	I_{PP}	–	–	17	A
Junction Capacitance Between I/O Pins and Ground @ V_R = 0 V, 1.0 MHz	C_J	–	–	400	pF

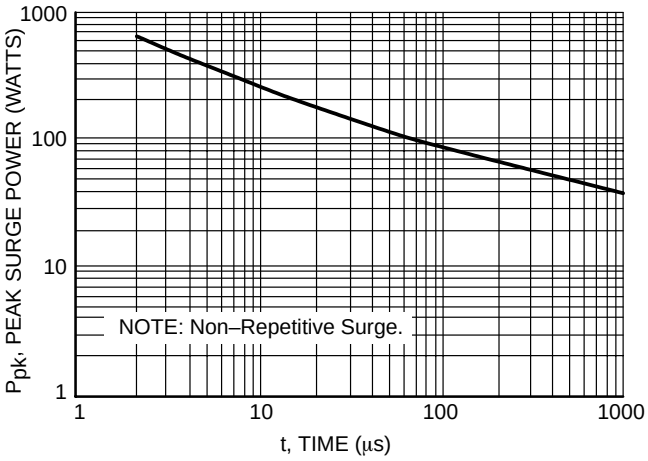


Figure 1. Pulse Width

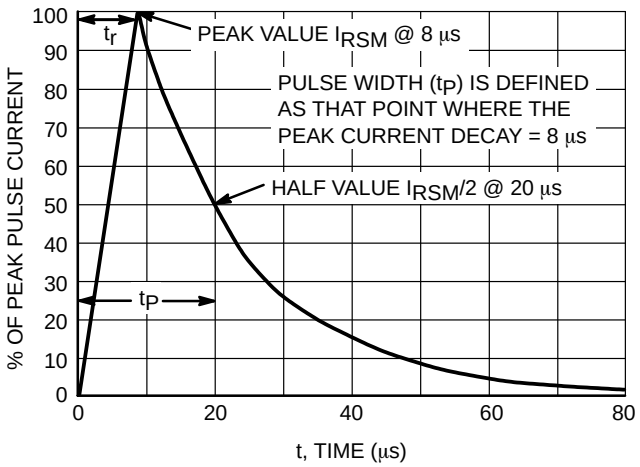


Figure 2. 8 × 20 μs Pulse Waveform

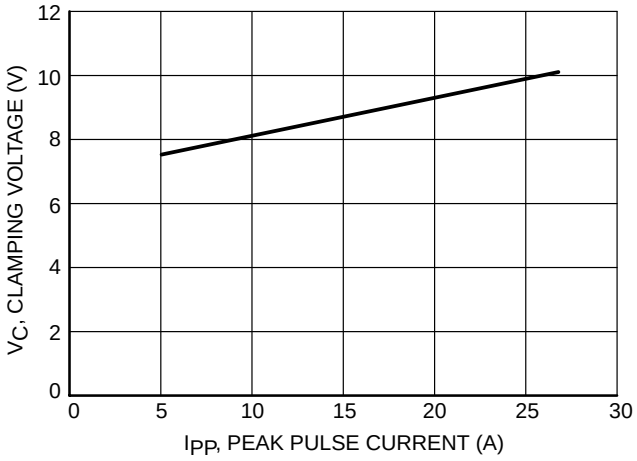


Figure 3. Clamping Voltage versus Peak Pulse Current

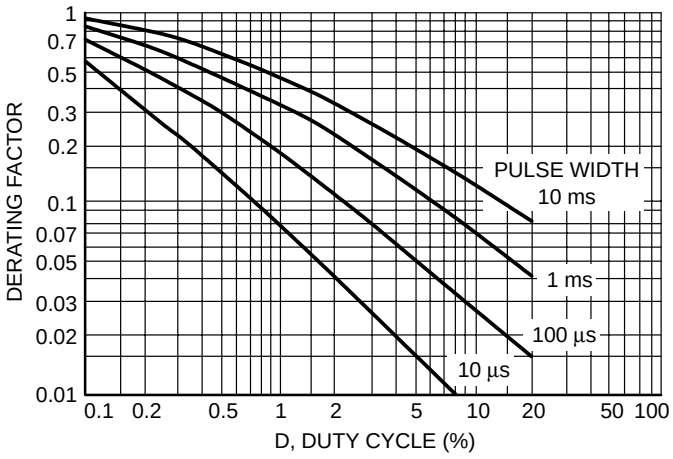


Figure 4. Typical Derating Factor for Duty Cycle

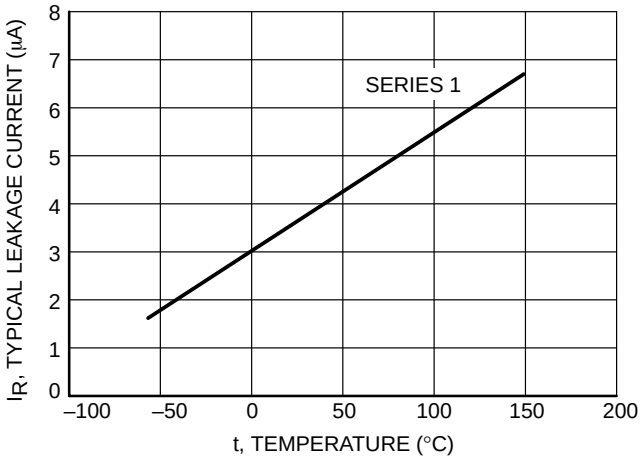
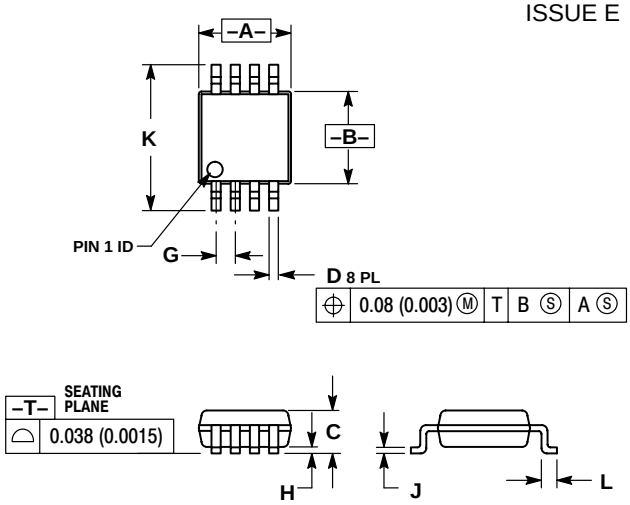


Figure 5. Typical Leakage Current versus Temperature

NUP6101DMR2

PACKAGE DIMENSIONS

Micro8
CASE 846A–02
ISSUE E



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH, PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	2.90	3.10	0.114	0.122
B	2.90	3.10	0.114	0.122
C	---	1.10	---	0.043
D	0.25	0.40	0.010	0.016
G	0.65 BSC		0.026 BSC	
H	0.05	0.15	0.002	0.006
J	0.13	0.23	0.005	0.009
K	4.75	5.05	0.187	0.199
L	0.40	0.70	0.016	0.028

Micro8 is a trademark of International Rectifier.

PUBLICATION ORDERING INFORMATION

Literature Fulfillment:
Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303–675–2175 or 800–344–3860 Toll Free USA/Canada
Fax: 303–675–2176 or 800–344–3867 Toll Free USA/Canada
Email: ONlit@hibbertco.com

N. American Technical Support: 800–282–9855 Toll Free USA/Canada

JAPAN: ON Semiconductor, Japan Customer Focus Center
4–32–1 Nishi–Gotanda, Shinagawa–ku, Tokyo, Japan 141–0031
Phone: 81–3–5740–2700
Email: r14525@onsemi.com

ON Semiconductor Website: http://onsemi.com

For additional information, please contact your local Sales Representative.